

TA8320F

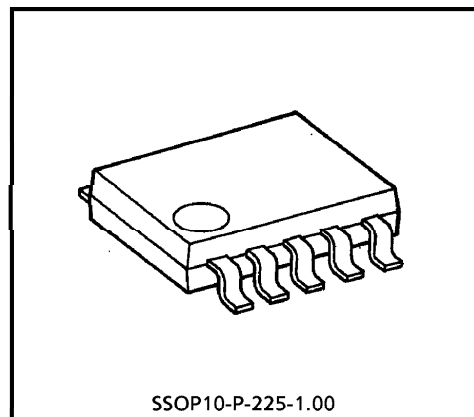
LED DRIVER FOR CAMERA

TA8320F is Multi Chip IC incorporates 3 low saturation discrete transistors.

This IC is suitable for a camera use LED drive applications.

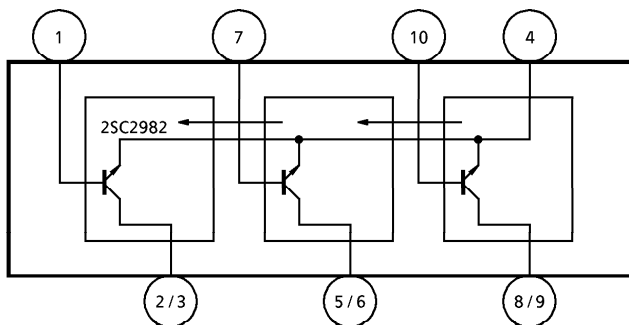
FEATURES

- Suitable for LED drive circuit.
- Small package sealed : SSOP10
- Low saturation voltage
- 3-channel sink type

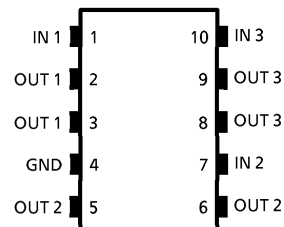


SSOP10-P-225-1.00
Weight : 0.10g (Typ.)

BLOCK DIAGRAM



PIN CONNECTION



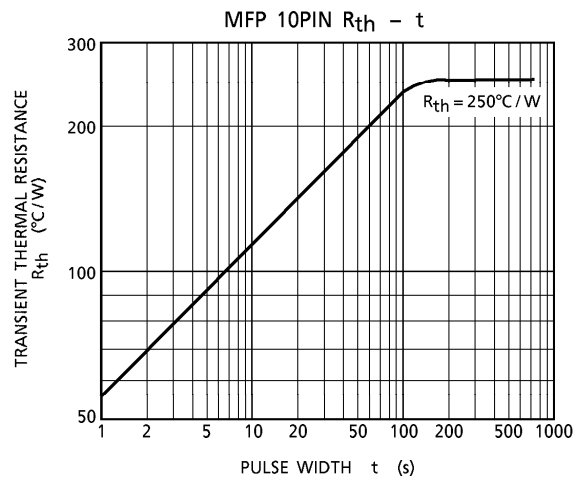
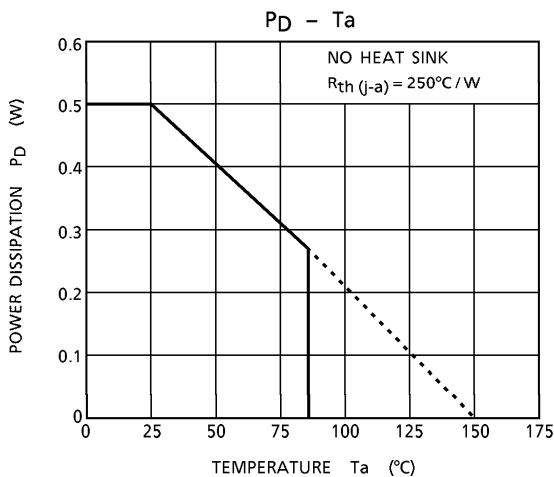
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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	10	V
Breakdown Voltage	V _{CB0}	10	V
	V _{CEO}	10	V
	V _{EBO}	6	V
Output Current	I _O	2	A
	I _{O (peak)}	(*) 4	
Base Current	I _B	0.4	A
	I _{B (peak)}	(*) 0.8	
Power Dissipation	P _D	590	mW
Junction Temperature	T _j	150	°C
Operating Temperature	T _{opr}	-40~85	°C
Storage Temperature	T _{stg}	-55~150	°C

(*) T = 10ms Max. and maximum duty is less than 30%



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

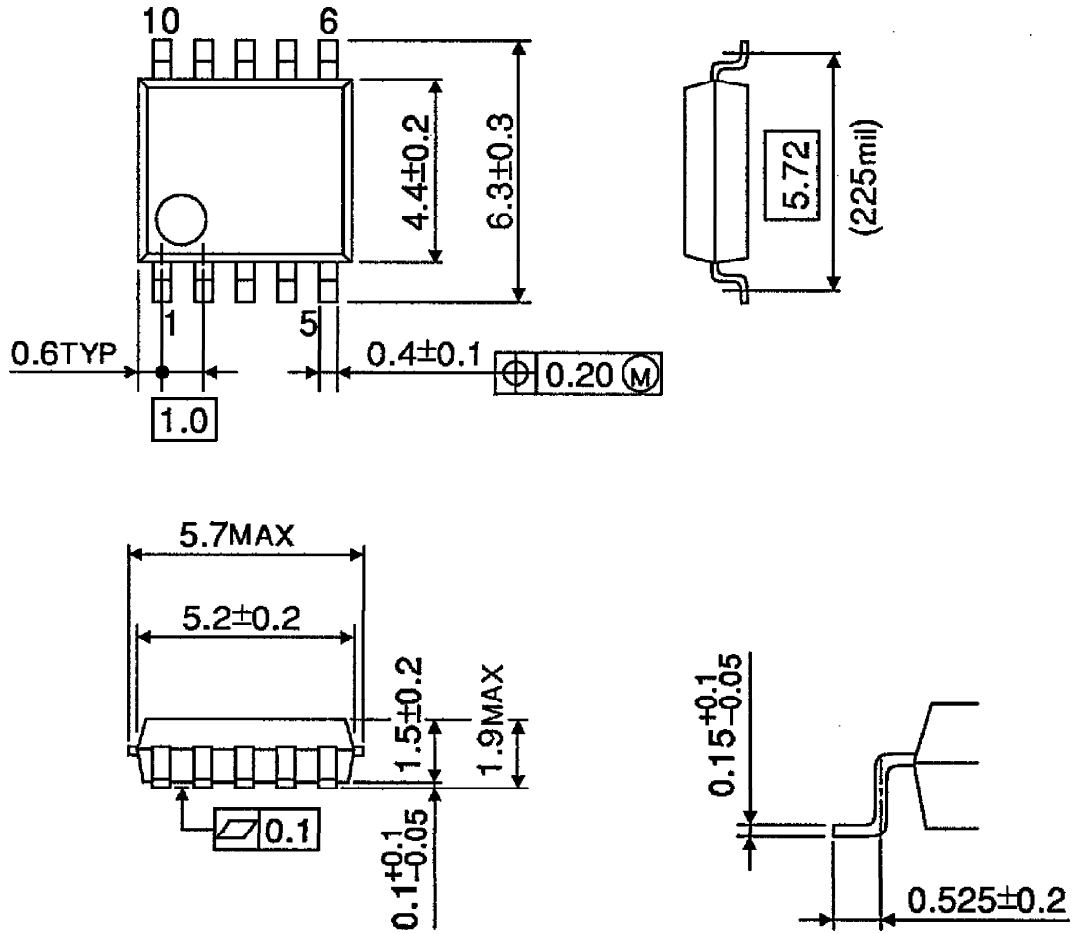
CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Gain	h _{FE (1)}	—	V _{CE} = 1V, I _C = 0.5A	160	—	600	
	h _{FE (2)}	—	V _{CE} = 1V, I _C = 2.0A	60	130	—	
Saturation Voltage	V _{CE (sat)}	—	I _C = 2A, I _B = 50mA	—	—	0.5	V
Transition Frequency	f _T	—	V _{CE} = 2V, I _C = 0.5A	—	150	—	MHz
Leakage Current	I _{OL}	—	V _{CC} = 10V	—	0	1.0	μA
Base-Emitter Forward Voltage	V _{BE}	—	V _{CE} = 1V, I _C = 2.0A	—	0.84	1.5	V

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OUTLINE DRAWING
SSOP10-P-225-1.00

Unit : mm



Weight : 0.10g (Typ.)